

Amendments to the Specification:

Please replace the three paragraphs on page 12 and the first paragraph on page 13 with the following amended paragraphs:

-- The reason for using the polysilicon instead of the tungsten is because polysilicon can be etched more deeply than tungsten during photolithography using a light source of ArF and a photoresist for ArF. Thus, an ultra fine patterning process providing a line-width below about 80 nm by employing the ArF photolithography can be applicable. Also, the polysilicon layer 24 has a better etch selectivity with respect to an oxide layer than the hard mask ~~hard-mask~~ nitride layer 23 does. Therefore, it is possible to reduce losses of the hard mask nitride layer 23 during a process for forming a contact hole by a self-aligned contact (SAC) process.

Herein, the hard mask ~~hard-mask~~ nitride layer 23 is formed with a relatively thin thickness ranging from about 900 Å to about 1500 Å. Preferably, the polysilicon layer 24 is initially formed with a thickness in a range from about 1000 Å to about 2000 Å and then remains in a thickness from about 300 Å to about 1000 Å.

Therefore, the total thickness of the hard mask decreases even with the hard mask with the dual structure, and thus, improving a gap-fill property while a subsequent insulation layer is deposited. During the bit line patterning process, there ~~dose~~ does not occur losses of the hard mask nitride layer 23. Hence, it is possible to determine the required thickness by being able to take account of any loss of other layers during subsequent processes except for the bit line patterning process. As a result of the above effect, it is further possible to improve process stability and reliability.

As shown in Fig. 2A, each bit line has a stack structure including the bit line conductive layer 22, the hard mask ~~hard-mask~~ nitride layer 23 and the polysilicon layer 24, and the plug 21 is formed between the bit lines. --

Please replace the third paragraph on page 14 with the following amended paragraph:

-- Next, the etch stop layer is removed by performing an etching process without using a mask so as to expose the plug 21. Thus, only a partial portion of the polysilicon layer 24 is etched away. Since the polysilicon layer 24 has a higher etch selectivity with respect to an oxide layer than that of the hard mask ~~hard-mask~~ nitride layer 23 during the formation of the line type contact hole 27, the loss of the hard mask polysilicon layer 24 is not high. --